

FileViewEditToolsWindowHelp

Pending

Active

Failed

Saved

L25: (6) (((select\$4 adj transistor) with (((Global main common) 0

L26: (20) (((Global main common) 0

L27: (26) 25 26

L28: (1) 09/956212

L30: (182712) short\$4 adj circuit\$4

L31: (2853) (((Global main common)) adj (bl bitline bit adj line 0)

L32: (52) 30 same 31

L33: (37123) select\$4 adj (transistor device)

L34: (12) 32 and 33

L35: (263) 30 and 31

L36: (83) 33 and 35

L29: (27) 27 28

(1) 09/948877

(1738) "KONINKLUKE PHILIPS".as.

(0) 10/604406

(1) 09/956212

(1) 6620670.pn.

(1) 09/653541

(785087) (bl bitline bit adj line readline read adj line sense adj line column)

(79745) (bl bitline bit adj line)

(10789) select\$4 adj transistor

BrowseQueueClear

DBs:USPAT,US POPUB,EPO,JPO,DI,AWENT,IBM,TTXO

Default operator:OR

Plurals

Highlight all hit terms initially

27 28

026 2 003

U	Invntor	Document#	Issue	P	Title	Current	CurrentX	Retrieval	S	C	P	Image Doc	P
1	Onakado, Ta	US 8172397	200104	4	Non-volatile semiconductor memory device	257/321	257/315;					US 817239	P
2	Shiba, Kazuy	US 6038170	200002	2	Semiconductor integrated circuit device incl	365/185	257/E21.66					US 603817	P
3	Wang, Chen-j	US 5545585	199601	1	Method of making a dram circuit with fin-sha	438/397	257/E21.01					US 554558	P
4	Hsu, Ching-Hs	US 2003005	200301	1	Nonvolatile semiconductor memory device h	365/185;						US 200300	P
5	Lee, Peter W.	US 6620682	200305	5	Set of three level concurrent word line bias	438/257	438/14;					US 662068	P
6	Parat, Krishn	US 2001002	200102	2	Novel flash integrated circuit and its method	438/259	438/257;					US 200100	P
7	Guo, Jyh-Chy	US 2001000	200102	2	Floating gate memory with substrate band-to	257/200	257/E28.30					US 200100	P
8	Lee, Yong-Ky	US 6583168	200301	1	Non-volatile semiconductor device with anti-	257/318	257/328					US 658316	P
9	Guo, Jyh-Chy	US 6352886	200202	2	Method of manufacturing floating gate mem	438/201	257/E28.30					US 635288	P
10	Parat, Krishn	US 6265282	200101	1	Method of fabrication of a novel flash integr	438/524	438/434;					US 626528	P